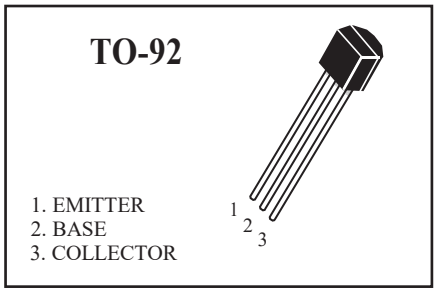
NPN General Purpose Transistors

Lead(Pb)-Free



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base VOltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	500	mAdc
Total Device Dissipation T_A=25 C	P_D	0.625	W
Junction Temperature	T_j	150	C
Storage, Temperature	Tstg	-55 to +150	°C

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I_C= 0.1 mAdc, I_B=0)	$V_{(BR)CEO}$	25	-	Vdc
Collector-Base Breakdown Voltage (I_C= 100 μAdc, I_E=0)	$V_{(BR)CBO}$	40	-	Vdc
Emitter-Base Breakdown Voltage (I_E= 100 μAdc, I_C=0)	$V_{(BR)EBO}$	5.0	-	Vdc
Collector Cutoff Current (VCE= 20 Vdc, I_B=0)	I_{CE0}	-	0.1	uAdc
Collector Cutoff Current (VCB= 40 Vdc, I_E=0)	I_{CBO}	-	0.1	uAdc
Emitter Cutoff Current (V_{EB}= 3.0Vdc, I_C=0)	I_{EBO}	-	0.1	uAdc

ELECTRICAL CHARACTERISTICS (T_A= 25 °C unless otherwise noted) (Countinued)

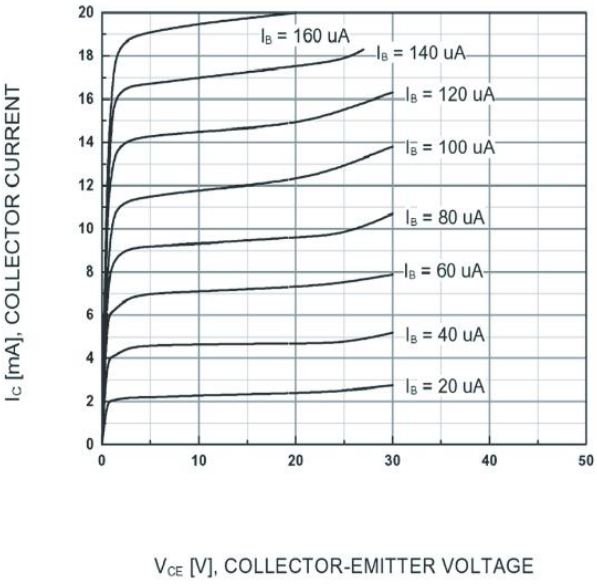
ON CHARACTERISTICS

Characteristics	Symbol	Min	TYP	Max	Unit
DC Current Gain (I_C= 50 Adc, V_{CE}=1.0 Vdc)	h_{FE} (1)	85	-	300	-
DC Current Gain (I_C= 500 mAdc, V_{CE}= 1.0 Vdc)	h_{FE} (2)	50	-	-	-
Collector-Emitter Saturation Voltage (I_C= 500 Adc, I_B= 50 mAdc)	$V_{CE(sat)}$	-	-	0.6	Vdc
Base-Emitter Saturation Voltage (I_C= 500 mAdc, I_B= 50 mAdc)	$V_{BE(sat)}$	-	-	1.2	Vdc
Current-Gain-Bandwidth Product (I_C= 20 mAdc, V_{CE}=6.0 Vdc, f=30MHz)	f_T	150	-	-	MHz

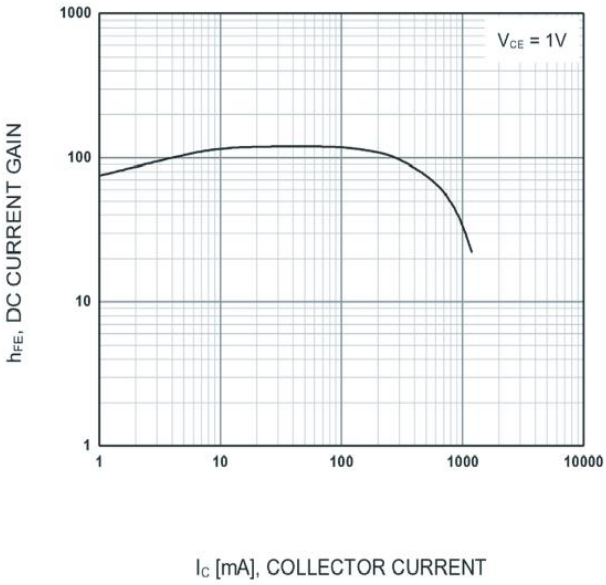
Classification of $h_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300

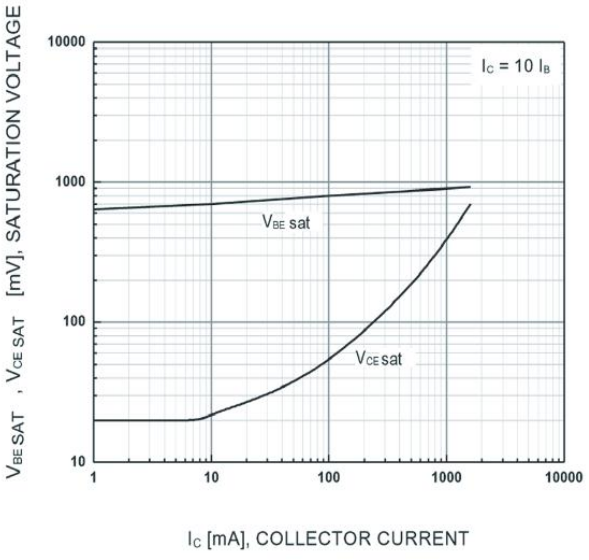
Typical Characteristics



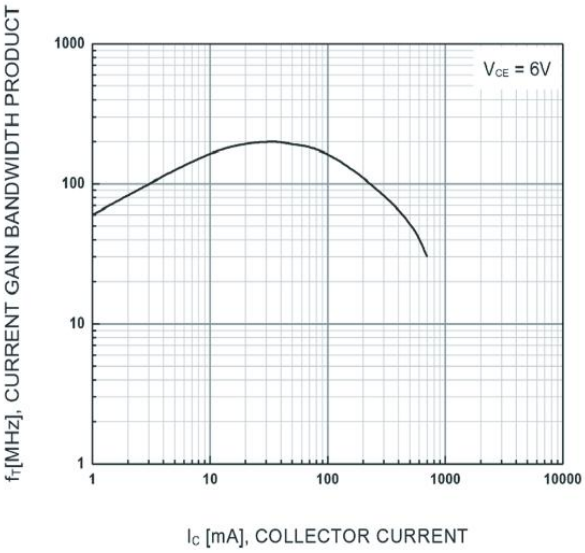
Static Characteristic



DC current Gain



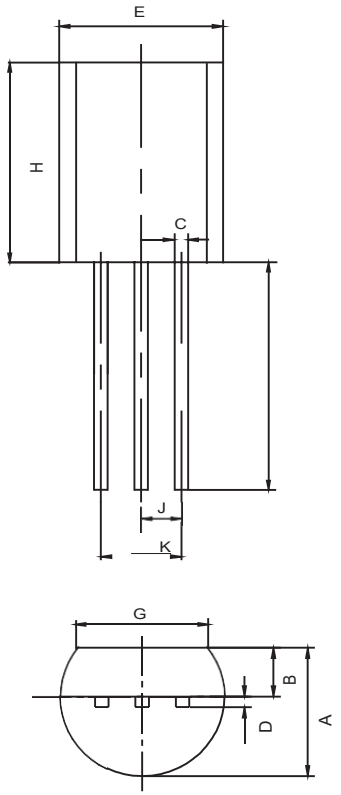
Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product

TO-92 Outline Dimensions

unit:mm



TO-92		
Dim	Min	Max
A	3.30	3.70
B	1.10	1.40
C	0.38	0.55
D	0.36	0.51
E	4.40	4.70
G	3.43	-
H	4.30	4.70
J	1.270TYP	
K	2.44	2.64
L	14.10	14.50

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